

STPS2045CH

Power Schottky rectifier

Datasheet - production data

Features

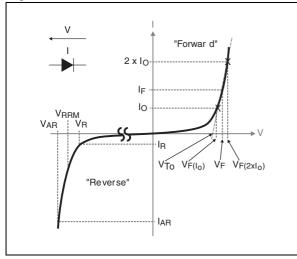
- Very small conduction losses
- Avalanche rated
- Low forward voltage drop
- High frequency operation

Description

This device is a dual diode Schottky rectifier, suited to high frequency switch mode power supply.

Packaged in IPAK, this device is intended to be used in notebook, game station and desktop adapters, providing in these applications a good efficiency at both low and high load.





 V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 8*. V_{AR} and I_{AR} are pulse measurements (t_p < 10 μs). V_R, I_R, V_{RRM} and V_F, are static characteristics

Table 1.Device summary

Symbol	Value
I _{F(AV)}	2 x 10 A
V _{RRM}	45 V
T _{j (max)}	175 °C
V _{F (max)}	0.57 V

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This is information on a product in full production.

June 2012

1 Characteristics

Table 2.	Absolute ratings	limiting values	nor diada)
Table 2.	Absolute ratings	(initiality values,	per diode)

Symbol	Parameter	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	Forward rms voltage			20	А
			Per diode	10	А
I _{F(AV)}	Average forward current $\delta = 0.5$	T _c = 150 °C	Per package	20	A
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sine-wave}$				А
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power $t_p = 10 \ \mu s, T_j = 125 \ ^{\circ}C$			280	W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage $t_p < 10 \ \mu s, T_j < 125 \ ^\circ C, I_{AR} < 4.7 \ A$			60	V
V _{ASM} ⁽²⁾	Maximum single-pulse peak avalanche voltage $t_p < 10 \ \mu$ s, T _j < 125 °C, I _{AR} < 4.7 A			60	V
T _{stg}	Storage temperature range			-65 to + 175	°C
Тj	Maximum operating junction temperature ⁽³⁾			+ 175	°C

1. For pulse time duration deratings, please refer to *Figure 4*. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

2. See Figure 8

3. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance parameters

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case Per Tota	r diode al	2.50 1.6	°C/W
R _{th (c)}	Coupling		0.7	°C/W

When the diodes 1 and 2 are used simultaneously:

 ΔT_{i} (diode 1) = P(diode1) x R_{th(i-c)}(Per diode) + P(diode 2) x R_{th(c)}

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Tests co	Min.	Тур.	Max.	Unit	
I _B ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V – V			100	μΑ
Reverse lea	neverse leakage current	$T_j = 125 \ ^{\circ}C$ $V_R = V_{RRM}$		7	15	mA	
		T _j = 125 °C	I _F = 10 A		0.5	0.57	
V _F ⁽²⁾ F	Forward voltage drop	T _j = 25 °C	I _F = 20 A			0.84	V
		T _j = 125 °C	F = 20 A		0.65	0.72	

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

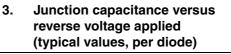
2. Pulse test: $t_p = 380 \ \mu s, \ \delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 0.42 \text{ x } I_{F(AV)} + 0.015 I_{F}^{2}(RMS)$



Figure 2. Average forward power dissipation Figure 3. versus average forward current (per diode)



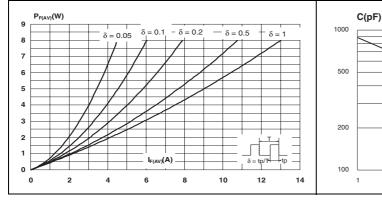


Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

V_R(V)

10

20

50

ТÍ

5

2

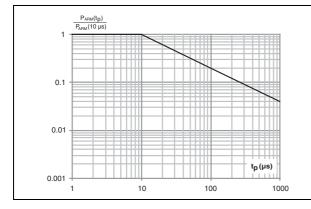


Figure 6. Reverse leakage current versus reverse voltage applied (typical values, per diode)

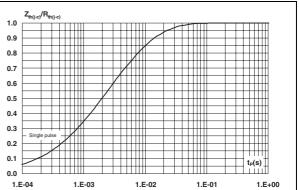
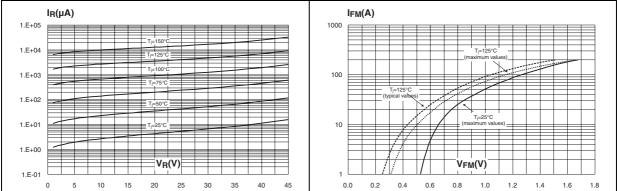


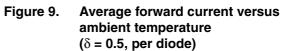
Figure 7. Forward voltage drop versus forward current (per diode)

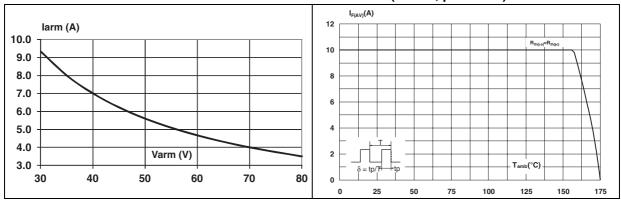




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Figure 8. Reverse safe operating area $(t_p < 10 \ \mu s \ and \ T_j < 125 \ ^\circ C)$





2 Package information

- Epoxy meets UL94, V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

Table 5. IPAK Dimensions

			Dimensions					
		Ref.	М	illimete	rs		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
		А	2.20		2.40	0.086		0.094
		A1	0.90		1.10	0.035		0.043
		A3	0.70		1.30	0.027		0.051
		В	0.64		0.90	0.025		0.035
		B2	5.20		5.40	0.204		0.212
		B3			0.95			0.037
		B5		0.30			0.035	
		С	0.45		0.60	0.017		0.023
		C2	0.48		0.60	0.019		0.023
	A1	D	6		6.20	0.236		0.244
V1		Е	6.40		6.60	0.252		0.260
e		e		2.28			0.090	
e, → B ⁵ , G,		G	4.40		4.60	0.173		0.181
		H		16.10			0.634	
		L	9		9.40	0.354		0.370
		L1	0.8		1.20	0.031		0.047
		L2		0.80	1		0.031	0.039
		V1		10°			10°	



3 Ordering information

Table 6.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS2045CH	S2045CH	IPAK	0.35 g	75	Tube

4 Revision history

Table 7.Document revision history

Da	ate	Revision	Changes
21-Ju	n-2012	1	First issue



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